

KSC5338F

High Voltage Power Switch Switching Application WWW.BZSC.COM

- High Speed Switching
- Wide SOA



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NPN Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units V	
V _{CBO}	Collector-Base Voltage	1000		
V _{CEO}	Collector-Emitter Voltage	450	V	
V _{EBO}	Emitter-Base Voltage	9	V	
I _C	Collector Current (DC)	5	Α	
I _{CP}	Collector Current (Pulse)	10	Α	
I _B	Base Current (DC)	2	Α	
I _{BP}	Base Current (Pulse)	4	A	
P _C	Collector Dissipation (T _C =25°C)	40	W	
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	- 65 ~ 150	°C	

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	1000			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	450			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _C =1mA, I _E =0	9			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 800V, V_{BE} = 0$			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$			10	μΑ
h _{FE1} h _{FE2}	* DC Current Gain	$V_{CE} = 5V, I_{C} = 0.5A$ $V_{CE} = 1V, I_{C} = 2A$	15 6	27	30	C.C.
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.1A$ $I_C = 2A, I_B = 0.4A$	-	0.55	0.8 0.5	V V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 1A, I_B = 0.1A$ $I_C = 2A, I_B = 0.4A$			1.1 1.25	V V
C _{ob}	Output Capacitance	V _{CB} = 10V, f =1MHz		70		pF
C _{ib}	Input Capacitance	V_{EB} =8V, I_{C} =0, f =1MHz		1000		pF
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.1A$		14		MHz
t _{ON}	Turn ON Time	$V_{CC} = 125V, I_{C} = 1A$			200	ns
t _{STG}	Storage Time	$I_{B1} = 0.2A, I_{B2} = -0.2A$			2	μs
t _F	Fall Time	$R_L=125\Omega$			500	ns

* Pulse Test: Pulse Width=5ms, Duty Cycle≤10%

Typical Characteristics

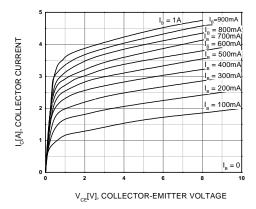


Figure 1. Static Characteristic

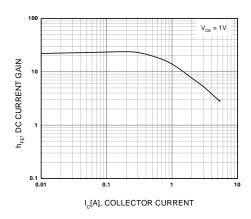


Figure 3. DC current Gain

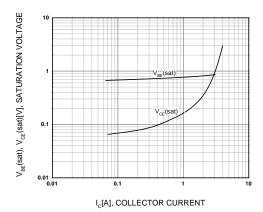


Figure 5. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

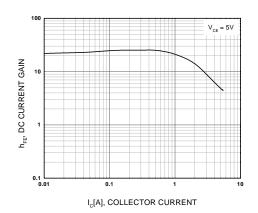


Figure 2. DC current Gain

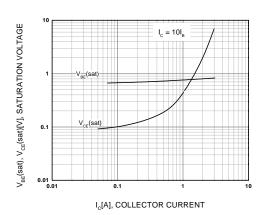


Figure 4. Base-Emitter Saturation Voltage Collect-Emitter Saturation Voltage

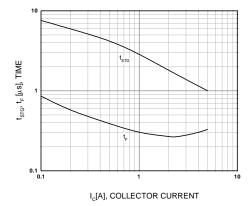


Figure 6. Switching Time

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Typical Characteristics (Continued)

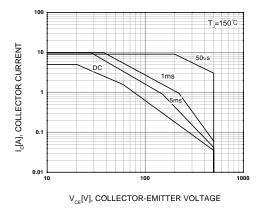


Figure 7. Safe Operating Area

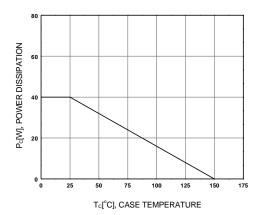
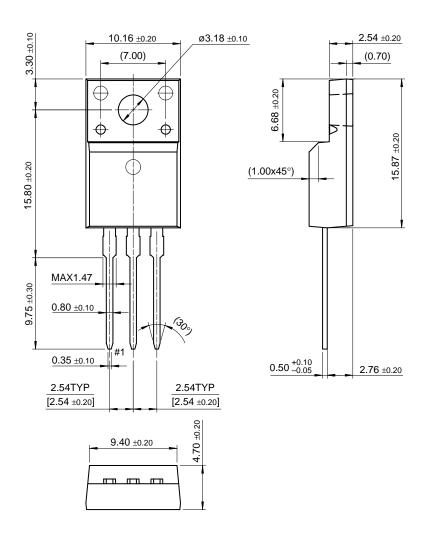


Figure 8. Power Derating

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Package Demensions

TO-220F



Dimensions in Millimeters

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